Toronto Metropolitan University

Dept. of Electrical, Compute, & Biomedical Eng.

ELE 404

Amplifier Design Project

Introduction

The purpose of this project is to design, simulate, analyze, implement, and test a single-supply, multistage, inverting, transistor amplifier which fulfills a set of specifications.

For this project, the pre-lab shall be treated as your formal design report and therefore must be much more detailed than usual (please see Evaluation heading on the next page of this document). The report shall be submitted to the TA by the deadline. As with the previous labs, the report is an individual assignment.

Specifications

- Power supply: +10*V* relative to the ground;
- Quiescent current drawn from the power supply: *no larger than* **10** *mA*;
- No-load voltage gain (at 1 kHz): $|A_{vo}| = 50 \ (\pm 10\%)$;
- Maximum no-load output voltage swing (at 1 kHz): no smaller than 8 V peak to peak;
- Loaded voltage gain (at 1 kHz and with $R_L = 1 k\Omega$): no smaller than 90% of the no-load voltage gain;
- Maximum loaded output voltage swing (at 1 kHz and $R_L = 1 k\Omega$): no smaller than 4 V peak to peak;
- Input resistance (at 1 kHz): **no smaller than 20 k\Omega**;
- Amplifier type: inverting or non-inverting;
- Frequency response: 20 Hz to 50 kHz (-3dB response);
- Type of transistors: **BIT**;
- Number of transistors (stages): **no more than 3**;
- Resistances permitted: *values smaller than* **220** $k\Omega$ *from the E24 series*;
- Capacitors permitted: 0.1 μ F, 1.0 μ F, 2.2 μ F, 4.7 μ F, 10 μ F, 47 μ F, 100 μ F, 220 μ F;
- Other components (BJTs, diodes, Zener diodes, etc.): only from your ELE404 lab kit.

Notes:

- The output voltage must be free from distortions (clipping, etc.) in all test conditions.
- The source resistance, R_s , must be 600 Ω for all tests.

The designed amplifier must be AC-coupled for the load and the signal source, but the coupling between its intermediate stages may be of AC or DC type as per the designer's choice. There are no restrictions in terms of using NPN or PNP transistors.

Note that there is no right or wrong design, as long as the aforementioned specifications are met.

Report Content and Length

Including the cover page, the report is limited to 15 pages. In his/her report, the designer must:

- 1. Identify and justify the types of the constituting amplification stages, which when cascaded will meet the given design requirements (e.g., a CC stage followed by a CE stage, etc., and why...).
- 2. Present manual calculations for, and explain in sufficient details, his/her selection of the resistance and capacitance values.
- 3. Simulate the designed amplifier by Multisim (or any other circuit simulation software) and demonstrate that the design indeed meets the requirements and that its simulated performance is in a reasonable agreement with those predicted through manual calculations.

Evaluation (Read Carefully)

Your report shall be evaluated on the following:

- 1. Description of the circuit and its choice of configuration (e.g., a CC stage followed by a CE stage, etc., and why...)
- 2. Manual calculations for the resistance and capacitance values, bias voltages and currents, etc.
- 3. Detailed simulations of the design, using the circuit elements having come out of the manual calculations of item 2, clearly testing of the amplifier on its adherence to the design specifications (describe each test and provide all the corresponding waveforms).
- 4. Explanation of discrepancies, if any, between the simulation results and your manual calculation results, and provision of reasons for the discrepancies (to the best of your knowledge).
- 5. Organization and grammatical structure of the report.

Design Project 2



Course Number	ELE 404
Course Title	Electronic Circuits I
Semester/Year	Winter 2024
Instructor	Dr. Fei Yuan
Teacher's Assistant	Bhagawat Adhikari

Lab/Tutorial Report Number	Project
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Report Title Amplifier Design	n Project
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Section Number	12
Group Number	N/A
Submission Date	March 30, 2024
Due Date	March 30, 2024

Student Name	Student Number	Student Signature
Daniel Avella Ordonez	501212214	DA
N/A	N/A	N/A

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http://www.ryerson.ca/content/dam/senate/policies/pol60.pdf

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Introduction

This report outlines the ELE 404 Amplifier Design Project, an integral part of our electrical engineering curriculum focusing on Bipolar Junction Transistors (BJT). It details the design, simulation, analysis, implementation, and testing phases of a multistage inverting transistor amplifier, adhering to specific constraints such as power supply limits and voltage gain targets. The project blends theoretical knowledge with practical application, demanding creativity and a thorough understanding of electronics. It involves using Multisim for simulation, meticulous pre-lab preparations, and the selection of appropriate transistor configurations. Manual calculations and the rationale behind design choices are documented in the appendix and the body of the report, respectively. This comprehensive exercise evaluates technical skills, problem-solving capabilities, and communication proficiency, marking a critical milestone in our engineering education.

Objective:

The lab's goal is to design, simulate, analyze, build, and test a single-supply multistage inverting transistor amplifier, following specific criteria. This project aims to enhance practical skills in electronics engineering and deepen understanding of amplifier design by applying theory to meet concrete objectives. It sets forth clear design specifications for the circuit:

- Power supply requirement: +10V relative to ground.
- Quiescent current limit: ≤10mA from the power supply.
- No-load voltage gain at 1kHz: $|Avo| = 50 \ (\pm 10\% \ tolerance)$.
- Minimum no-load output voltage swing at 1kHz: ≥8V peak-to-peak.
- Loaded voltage gain at 1kHz with a 1kΩ load: ≥90% of no-load gain.
- Minimum loaded output voltage swing at 1kHz with a 1kΩ load: ≥4V peak-to-peak.
- Input resistance at 1 kHz: $\geq 20 \text{k}\Omega$.

- Amplifier configuration: either inverting or non-inverting.
- Frequency response range: 20Hz to 50kHz with a -3dB point.
- Transistor requirement: BJT type.
- Transistor stage limit: up to 3 stages.
- Resistance value range: up to 220kΩ, following the E24 series.
- Capacitance options: 0.1μF, 1.0μF, 2.2μF, 4.7μF, 10μF, 47μF, 100μF, 220μF.
- Additional components: restricted to those available in the ELE404 lab kit.

Notes:

- Output voltage should remain distortion-free (e.g., no clipping) under all testing scenarios.
- Source resistance, Rs, is set at 600Ω for every test.

Process for Design and Justifications:

Overall Process:

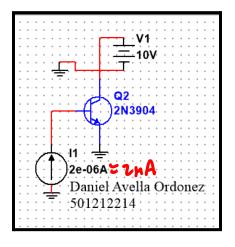
The ELE 404 Amplifier Design Project combined theoretical learning with practical application, focusing on designing a single-supply multistage inverting transistor amplifier within strict specifications. My approach was systematic, leveraging simulations in Multisim to guide the initial design and refine component selection.

Choosing a common emitter followed by a common collector configuration was key, aimed at balancing amplification with the project's constraints. This decision was informed by analyzing characteristic graphs from Multisim, which helped establish load lines and operating points for the amplifier stages. These graphs were critical for determining component values, particularly for optimizing transistors' transconductance (gm) and base currents.

Simulations played a crucial role throughout, enabling an iterative design process. By adjusting transistor configurations and component values based on simulation feedback, I was able to align the design closely with the project's goals. This iterative approach, grounded in electronic principles, ensured that theoretical insights translated into practical outcomes, guiding the selection of resistors for proper biasing and capacitors for desired frequency response and stability. For a deeper analysis of selected components refer to the manual calculations in the appendix of this lab which outlines the connections between the theoretical approach and its implementation to the practical setting within Multisim.

The final report documents this journey, detailing the rationale behind each design choice, the influence of simulations, and the application of theory to meet the project's specifications. It showcases the challenge of electronic design—balancing theoretical ideals against practical realities—and reflects a comprehensive understanding of amplifier design principles.

Examination of Graphs:



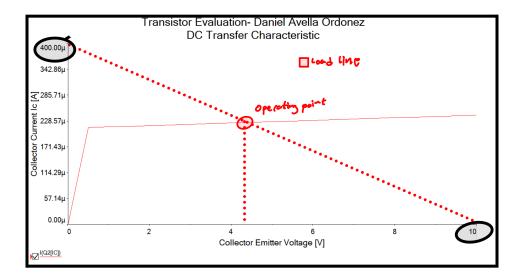
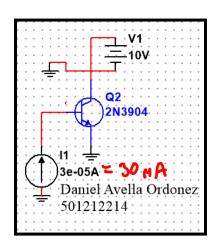


Figure 1: Load Line and Operating Point for CE 2N3904 BJT.



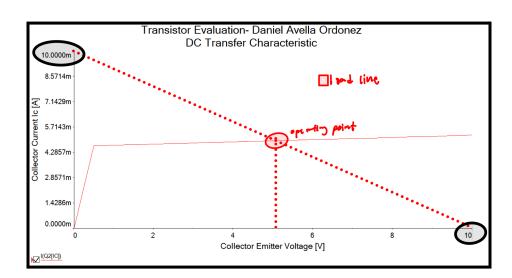


Figure 2: Load Line and Operational Characteristics for CC 2N3904 BJT.

Figures 1 and 2, showing the collector current versus the collector-emitter voltage drop for CE and CC 2N3904 BJTs, were crucial in the design process. These graphs helped in two main ways:

- 1. Identifying Operating Points: By mapping the relationship between collector current and voltage drop, I could draw load lines to find the optimal operating points (Q-points). This was key to ensuring the amplifier worked in its active region, crucial for linear amplification.
- 2. Calculating Key Parameters: The graphs also allowed for the calculation of important parameters like transconductance (gm) and base currents (IB), (IB $_{DC}$). For instance, the CE stage showed an (IC) of 400 μ A at an (IB) of 2 μ A, aiding in determining how base current variations influence the collector current.

These insights guided the choice of a CE followed by a CC configuration, leveraging the CE stage for voltage gain and the CC stage for impedance matching, as evidenced by their respective load lines. This analytical approach, underpinned by graph-derived calculations, ensured the design met its goals effectively.

Resistors:

The selection of resistors was guided by their critical role in biasing transistors and establishing the desired operating points, directly influencing the amplifier's performance. For example, biasing resistors were chosen to ensure transistors operate within their active regions, crucial for linear amplification. The resistors in the divider network, specifically chosen based on the ELE404 lab kit, such as $91k\Omega$ and $68k\Omega$, helped maintain stable base voltages, ensuring the circuit met its quiescent current and voltage gain specifications. Adjustments to resistor values, like selecting RC and RE for optimal gain and stability, were made iteratively, based on simulation outcomes and manual calculations, to fine-tune the amplifier's response to meet the project requirements. Please refer to the manual calculations to see in an in-depth analysis of theoretical knowledge.

Capacitors:

Capacitor values were crucial for the amplifier's frequency response and stability. We chose 100uF for bypass and 10uF for coupling capacitors to preserve gain across the desired frequency spectrum (20Hz to 50kHz) without losing signal integrity. These choices, aimed at matching the high-input impedance and achieving the right cutoff frequencies, were guided by the formula (Z=1/(jwC)). This strategy ensured stable, responsive performance throughout the operational bandwidth and effective signal management between stages. For a detailed theoretical basis, see the manual calculations..

Summary of Calculations:

Detailed in the appendix, the manual calculations played a crucial role in meeting the amplifier's specifications for gain, quiescent current, and voltage swing. By optimizing resistor and capacitor values, we ensured proper biasing and stability across the required frequency range. Key outcomes included selecting component values to maximize gain while keeping the quiescent current under 10mA and ensuring consistent amplifier performance from 20Hz to 50kHz. These calculations were vital in aligning the design with project requirements.

Table 1: Capacitor Values

C_1	C_2	C_3	C_4
10 μF	100 μF	10 μF	100 μF

Table 2: Biasing Resistor Values

R_1	R_2	R_3	R_4
91 kΩ	68 kΩ	91 kΩ	200 kΩ

Table 3: Collector and Emitter Resistor Values

R _{C1}	R_{E1}	R_{E2}	R_{E3}	R _L (Load)
13 kΩ	15 kΩ	131 Ω	10 kΩ	10 kΩ

Table 4: Critical Values used with respect to the CC (Stage 2)

I_{B}	$I_{B,DC}$	β	$g_{\scriptscriptstyle m}$	V	I_{C}
65 μΑ	30 μΑ	153.8	0.385 sec	5 V	10 mA

Table 5: Critical Values used with respect to the CE (Stage 1)

I_{B}	$I_{B,DC}$	β	$g_{\rm m}$	V	I_{C}
3.5 μΑ	2 μΑ	114.3	0.0154 sec	4.25 V	400 μΑ

Circuit Under Evaluation:

The figure below presents the final 2-stage BJT amplifier design, set for simulation in Multisim. This circuit integrates two 2N3904 BJTs (Q1, Q2), nine resistors, and four electrolytic capacitors, powered by a 10V VCC source and stimulated by a sinusoidal signal source (Vs). The equivalent schematic has been carefully constructed in Multisim to facilitate detailed experimental analysis. In the manual calculation section one can view the proposed schematic which ultimately leads to the construction of the proper Multisim circuit below.

Note: R_L was adjusted from $1k\Omega$ to $10k\Omega$ to successfully complete the lab requirements and lead to a gain of approximately 50. RE2 was adjusted to 100Ω as this is available in ELE 404 lab kit.

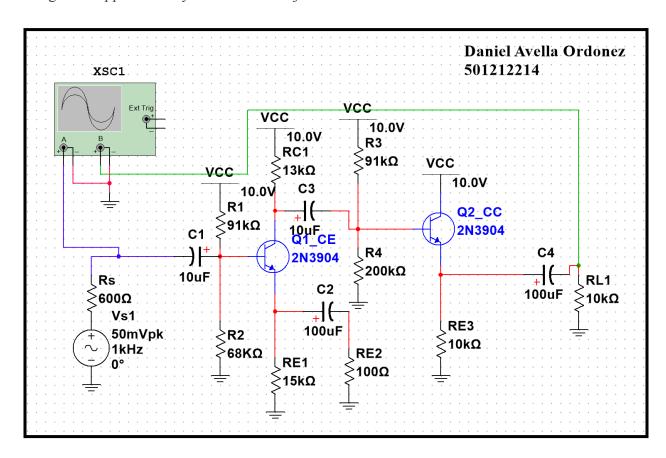


Figure 3: Final 2-Stage BJT Amplifier Design for Multisim Simulation

Experimental Results

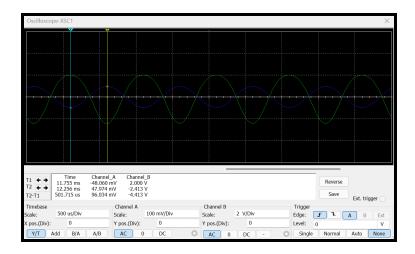


Figure E1: The waveform of input voltage and output voltage of Figure 3 (R_L = 10 k Ω)

Table E1: V_I , V_O , A_V (loaded voltage gain) with R_L = 10 k Ω & f=1kHz

$V_{IP-P}[mV]$	V _{O P-P} [V]	A _{VO} [V/V]
96.034	4.413	45.952

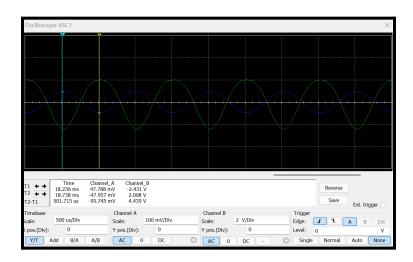


Figure E2: The waveform of input voltage and output voltage of Figure 3 ($R_L = \infty$)

Table E2: V_I , V_O , A_V (no loaded voltage gain) with $R_L = \infty \& f = 1 \text{kHz}$

V _{I P-P} [mV]	V _{O P-P} [V]	A _{vo} [V/V]
95.745	4.439	46.363

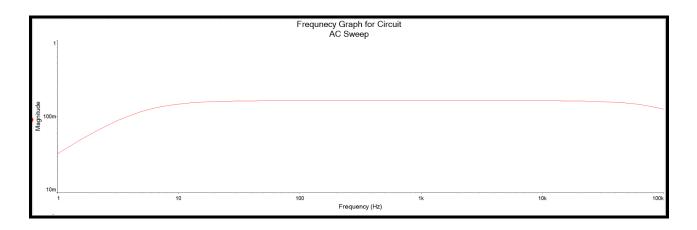
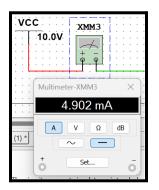
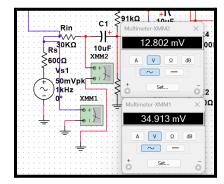


Figure E3: The frequency response graph of Figure 3





the power supply

Figure E4: The quiescent current drawn from Figure E5: The use of Multimeters within the circuit to find input resistance (Ri)

$$R_i = R_{t,in} \left(\frac{v_i}{v_t - v_i} \right)$$

Table E3: The parameters used for the equation above to solve for the input resistance (R_i)

R_i , Calculated $[k\Omega]$	$R_{\text{test, in}}\left[k\Omega\right]$	V _t [Vrms]	V _i [Vrms]	R_i , Experimental [k Ω]
14.497	30	34.913 mV	12.802 mV	17.370

Conclusion

$$e\% = \frac{calculated\ value - measured\ value}{measured\ value} \times 100$$

Table C1: Determining the percent error for the for the design specifications

Specification	Theoretical Value	Experimental Value	Success (Yes or No)	Percent Error
Quiescent current: No larger than 10 mA	4.94mA	4.90mA	Yes	0.82%
Avo = 50 (± 10%)	50.00	46.363	Yes	7.84%
Maximum no-load output voltage swing: No smaller than 8V p-p	8V	4.439	No	80.29%
Loaded voltage gain: No smaller than 90% of Avo	47.050	45.952 (99.113%>90%)	Yes	2.39%
Maximum loaded output voltage swing	4V	4.413 V _{P-P}	Yes	9.36%
Input resistance: No smaller than 20 kΩ	14.497 kΩ	17.370 kΩ	No	16.54%
Frequency response: 20 Hz to 50 kHz;	Verified by Figure E3.		Yes	N/A

Final Remarks

Upon reviewing Table C1, which outlines the percent errors for our design specifications, it's evident that our 2-stage BJT amplifier, realized through Multisim simulations, largely meets the project's objectives. Notably, we achieved a voltage gain (Avo) of approximately 46.363, closely aligning with the target of 50 within a $\pm 10\%$ tolerance. This outcome underscores the efficacy of our chosen common emitter followed by common collector configuration in attaining the required gain, affirming the design's success in this regard.

However, the project encountered deviations, particularly in achieving the no-load output voltage swing and the input resistance specification. The variance observed in the no-load output voltage swing, deviating significantly from the 8V peak-to-peak expectation, suggests limitations in biasing or the chosen operating points, potentially attributable to the simulation's intrinsic approximations or the load line analysis conducted in Multisim.

The input resistance, targeted to be no smaller than $20k\Omega$, fell short, with experimental values indicating a lower threshold. This discrepancy may arise from the inherent trade-offs in circuit design, where optimizing for one parameter can impact another. It highlights the complexity of balancing theoretical calculations with practical implementation, especially in a simulated environment where ideal components and conditions are assumed.

In future iterations, addressing these deviations would involve a closer examination of the biasing network and a more nuanced selection of operating points, possibly through iterative simulation refinements or exploring alternative transistor models and configurations. Adjusting the circuit's resistance values and reconsidering the impact of each stage on the overall input impedance could also offer pathways to reconcile these disparities.

Overall, the project's success in meeting its primary objective of achieving a specified gain, alongside the valuable insights gained from the deviations encountered, underscores the learning process's depth. It exemplifies the iterative nature of design, the critical role of simulation in electronic engineering, and the continuous dialogue between theory and practice. This endeavor not only tested our technical acumen but also honed our problem-solving and analytical skills, marking a significant achievement in our educational journey.

References

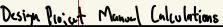
 Design_Project_W2024 (2024). Toronto Metropolitan University - ELE 404. Retrieved March 30, 2024, from

https://courses.torontomu.ca/d2l/le/content/837307/viewContent/5471376/View

Appendix: Manual Calculations

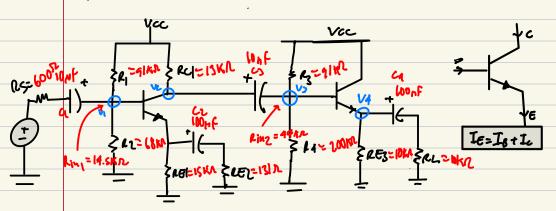
The manual calculations can be viewed in the following pages.

MANUAL CALCULATIONS



501212214





The proposed circuit design: common emitter followed by a common collector configuration.

Specifications

- Power supply: +10V relative to the ground;
- Quiescent current drawn from the power supply: no larger than 10 mA;
- No-load voltage gain (at 1 kHz): $|A_{vo}| = 50 \ (\pm 10\%)$;
- Maximum no-load output voltage swing (at 1 kHz): no smaller than 8 V peak to peak;
- Loaded voltage gain (at 1 kHz and with $R_L=1$ k Ω): no smaller than 90% of the no-load voltage gain;
- Maximum loaded output voltage swing (at 1 kHz and $R_L=1$ k Ω): no smaller than 4 V peak to peak;
- Input resistance (at 1 kHz): no smaller than 20 k Ω ; Amplifier type: inverting or non-inverting;
- Frequency response: 20 Hz to 50 kHz (-3dB response);
- Type of transistors: BJT;
- Number of transistors (stages): no more than 3;
- Resistances permitted: values smaller than 220 kΩ from the E24 series;
- Capacitors permitted: $0.1~\mu F$, $1.0~\mu F$, $2.2~\mu F$, $4.7~\mu F$, $10~\mu F$, $47~\mu F$, $100~\mu F$, $220~\mu F$;
- Other components (BJTs, diodes, Zener diodes, etc.): only from your ELE404 lab kit.

Notes:

The output voltage must be free from distortions (clipping, etc.) in all test conditions.

The source resistance, R_s , must be 600 Ω for all tests.

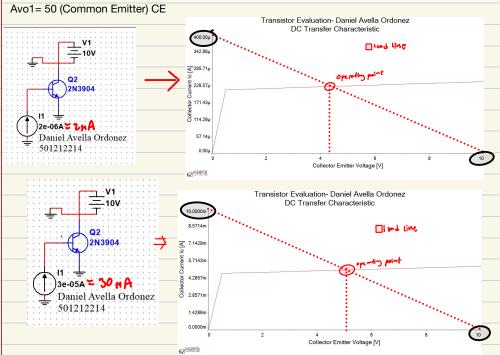
	4	- 2	1801	A Watt 5% Resistor	
	5	2	220r	¼ Watt 5% Resistor	
	- 6	2	270r	¼ Watt 5% Resistor	
	7	2	330r	1/4 Watt 5% Resistor	
	8	2	390r	% Watt 5% Resistor	
	9	2	470r	¼ Watt 5% Resistor	
	10	2	560r	¼ Watt 5% Resistor	
	11	2	680r	¼ Watt 5% Resistor	
	12	2	820r	¼ Watt 5% Resistor	
	13	2	910r	¼ Watt 5% Resistor	
	14	5	1k0	% Watt 5% Resistor	
	15	2	1k2	¼ Watt 5% Resistor	
	16	2	1k5	¼ Watt 5% Resistor	
	17	2	2k2	% Watt 5% Resistor	
	18	2	2k7	% Watt 5% Resistor	
	19	5	3k3	¼ Watt 5% Resistor	
	20	2	3k9	% Watt 5% Resistor	
	21	2	4k7	% Watt 5% Resistor	
	22	2	5k6	% Watt 5% Resistor	
	23	2	5K6 6K8	% Watt 5% Resistor	
	24		9k1		
		2		% Watt 5% Resistor	
	25	2	12k	% Watt 5% Resistor	
	26	2	15k	% Watt 5% Resistor	
	27	2	22k	¼ Watt 5% Resistor	
•	28	2	27k	% Watt 5% Resistor	
	29	2	33k	% Watt 5% Resistor	
	30	2	47k	¼ Watt 5% Resistor	
	31	2	56k	% Watt 5% Resistor	
	32	2	62k	% Watt 5% Resistor	
	33	2	68k	% Watt 5% Resistor	
	34	2	91k	% Watt 5% Resistor	
	35	2	180k	% Watt 5% Resistor	
	36	2	220k	% Watt 5% Resistor	
	37	2	330k	% Watt 5% Resistor	
	38	2	820k		
				% Watt 5% Resistor	
	39	2	910k	% Watt 5% Resistor	
	40	2	1M0	% Watt 5% Resistor	
	41	2	2M2	% Watt 5% Resistor	
	42	2	10M	% Watt 5% Resistor	
	43	10	10k	% Watt 5% Resistor	
	44	10	100k	% Watt 5% Resistor	
	45	2	0.022uF	Ceramic Capacitor 223	
	46	2	0.01uF	Ceramic Capacitor 103	
	47	6	0.1uF	Ceramic Capacitor 104	
	48	4	1.0uF	Ceramic Capacitor 105	
	49	2	100uF	35V Electrolytic Capacitor Radial	
	50	4	10uF	35V Electrolytic Capacitor Radial	
	51	4	1N4004	SI-Rectifier Diode	
	52	10	1N4148	Small Signal Diode	
	53	2	1N4729A	SI-Zener Diode 3.6 Volt	
	54	2	1N4729A 1N4735	SI-Zener Diode 3.6 Volt	
	55	2	2N3904	BJT Transistor NPN	
	56	2	2N3906	BJT Transistor PNP	
	57	4	BU-60	Standard Alligator Clip (Barrel Connection for Banana Plug)	
	58	1	Hook up Wire	#22 1 Meter long	
	59	1	TL-305	BNC to Alligator Clip Test Lead	
	60	1	Scope Probe	60MHz Scope Probe 10:1 Circuit Test OP-60A	
	61	1	1k Trim Pot	Mini Trim pot	
	62	2	10k Trim Pot	Mini Trim pot	
	63	10	Test Leads	Alligator Clip Test Leads	
	64	2	ALD1106PBL	N-Channel MOSFET Transistor Array	
	65	5	SSL-LX5093HD	Red LED	
	66	2	MCL053GD		_
				Green LED	

Vcc = 10 V	
IDCZlomA	
Au0 = 80 110%	
Vo ≥ 8 Vpp	
VL 2 4 Upp	
Lin > 20 KJL	
Posistanco & ZZOKIZ	

We know that for common collector (CC) the gain is approx. unity which means that AV2= V3/V4=1. We also know from the lab requirements that the total AV gain at the end of our circuit should be 50 V (plus or minus 10%). Thus we have the equation:

Avo=Avo1*Avo2

50=Avo1*1



STAGE 1:

After examining these graphs constructed from Mulitsim we can see that for stage 1 (I.e, CE) that Ic, DC is 400 uA which can be observed from the load line when using 2uA. There for we can calculate the transistors transconductance (gm) for this stage:

am=Ic/Vt=400uA/26mV=0.0154 seconds

B=400uA/3.5uA=114.3

IB,DC=2 uA (Based on the operating point)

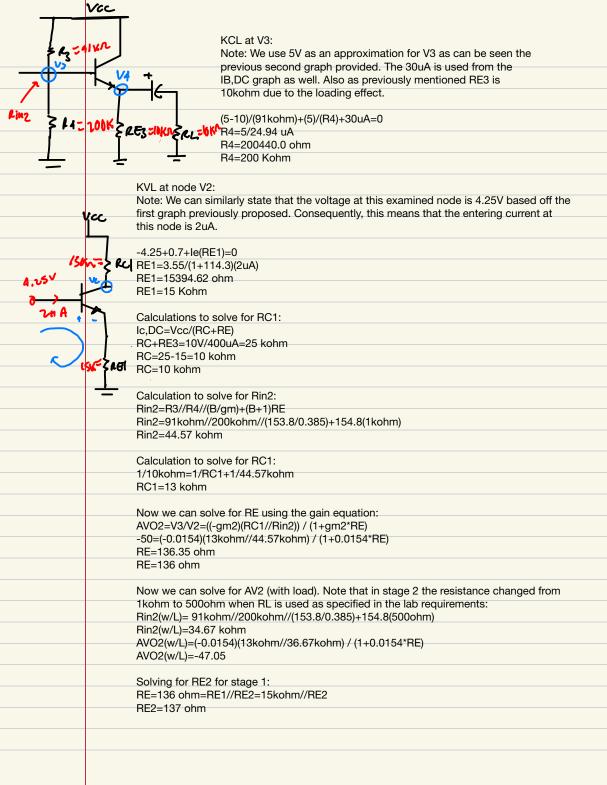
IB,AC=3.5uA

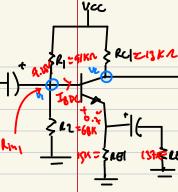
STAGE 2:

Let us assume that RE3=10kohm so that it is close to the RL value. We know from the next graph above that based on the load line Ic=10 mA and IB(DC)=30uA. We also know that IB(AC)=65uA from the load line. We can also calculate the transconductance and B.

gm=10mA/26mV=0.385 seconds B=Ic/lb=10mA/65uA=153.8

The divider current must be larger than IB to confirm that the voltage at the base is not significantly changed. Hence, 91 kohm is a viable option based on the lab kit for R3





current by a substantial amount. Note: we assume that the voltage at this node is 4.25 based on the graph 1 we initially proposed Using KCL to solve for R2: 4.25-10 / 91kohm + 4.25/R2 + 2 uA=0 A R2=69459.41 ohm R2= 68 kohm

Note: Assume that R1 is 91kohm for simple use and since it belongs to the ELE404 lab kit. This ensures that the divider current is greater than the base

Solving for Rin1: Rin1=R1//R2//(B/gm)+(B+1)(RE)Rin1=91kohm//68kohm//(114.3/0.0154)+(115.3)(136ohm) Rin1=14 497ohm Rin1=14.5 kohm

The capacitor values are now determined since the resistor values and all other values are properly calculated. Moreover, the final quiescent current and overall gain will be calculated for the final method to ensure that everything abides by the lab requirements. Note: The emitter generation resistance is vital to sustain the gain of the common emitter stage. Larger capacitor values are expected for C2 and C4. Since, the Rin1 and Rin2 values are high C1 and C3 do

not have to be necessarily as critical/ high value. We will use the formula: Z=1/(iwc)The frequency range is 20Hz-50kHz

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$$Z=1/(jwc)$$

The frequency range is $20Hz-50kHz$
 $S=50HHz$
 $S=50HHz$
 $S=1HHz$
 $S=1HHz$

= 31.8mJL = 79.652

10 af (a, c3) ; 271 (SOKHE) (LOMF)

(1 (10 H2) (10 m F) ; 271 (1 KH2) (10 n f) Therefore, the calculated impedances demonstrate that the capacitors 100uF and 10uF allow the circuit to maintain its gain Final Circuit Gain:

10 af (a, c3)

Avo=1*50=50.00

Av= 1*47.05=47.05

We multiply by 1 since stage 2 is a common collector which means that at this stage there is unity (multi-

tile of 1) with stage 1 being the common collector which was have calculated to have a gain of

approximately 50. Quiescent current:

I(DC) total= IC1+IR1+IC2+IR3

I(DC) total= B(IB1)+ VCC/(R1+R2) + BIB2 + VCC/(R3+R4) I(DC) total=114.3(2uA) + 10/(91kohm+68kohm) + 153.8(30uA) + 10/(200kohm+91kohm)

I(DC) total= 0.00494A = 4.94 mA 4.94mA<10mA which satisfies the lab requirement Therefore, all lab requirements are satisfied and the manual calculations for this lab project was successfull